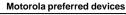
Advance Information TRIACS Silicon Bidirectional Thyristors

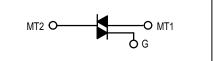
Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

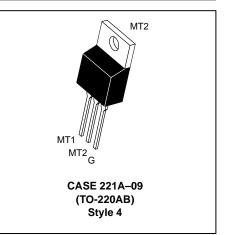
- Blocking Voltage to 800 Volts
- On-State Current Rating of 4.0 Amperes RMS at 100°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- High Surge Current Capability 40 Amperes
- Industry Standard TO-220AB Package
- High Commutating di/dt 6.0 A/ms minimum at 125°C











MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage $(T_J = -40 \text{ to } 125^{\circ}\text{C}, \text{ Sine Wave, 50 to 60 Hz, Gate Open})$	MAC4M MAC4N	Vdrm Vrrm	600 800	Volts	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 100°C)		I _{T(RMS)}	4.0	A	
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, TJ = 125°C)		ITSM	40	A	
Circuit Fusing Consideration (t = 8.33 ms)		l ² t	6.6	A ² sec	
Peak Gate Power (Pulse Width \leq 1.0 µs, T _C = 100°C)		PGM	0.5	Watts	
Average Gate Power (t = 8.3 ms, $T_C = 100^{\circ}C$)		PG(AV)	0.1	Watts	
Operating Junction Temperature Range		ТJ	-40 to +125	°C	
Storage Temperature Range		T _{stg}	-40 to +150	°C	
THERMAL CHARACTERISTICS		•		•	
Thermal Resistance — Junction to Case — Junction to Ambient		R _{θJC} R _{θJA}	2.2 62.5	°C/W	

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

 T_L

Preferred devices are Motorola recommended choices for future use and best overall value.

Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds



°C

260

MAC4M MAC4N

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
IDRM	Peak Repetitive Blocking Current $(V_D = Rated V_{DRM}, Gate Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$			0.01 2.0	mA		

ON CHARACTERISTICS

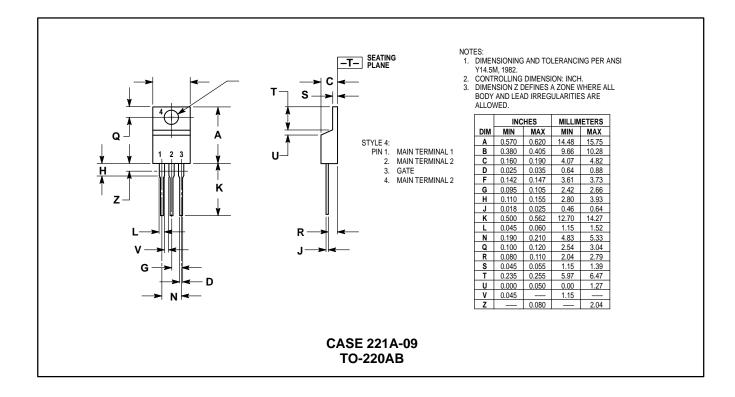
VTM	Peak On-State Voltage ¹ $(I_{TM} = \pm 6.0 \text{ A})$	_	_	1.6	V
I _{GT}	Gate Trigger Current (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	8.0 8.0 8.0		35 35 35	mA
ΙΗ	Holding Current (V _D = 12 V, Gate Open, Initiating Current = ±200 mA)	6.0	_	35	mA
ιL	Latching Current ($V_D = 12 \text{ V}, I_G = 10 \text{ mA}$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	 		60 80 60	mA
V _{GT}	Gate Trigger Voltage (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	0.5 0.5 0.5		1.3 1.3 1.3	V

DYNAMIC CHARACTERISTICS

(di/dt) _C	Rate of Change of Commutating Current ¹ (V _D = 400 V, I _{TM} = 4.0 A, Commutating dv/dt = 18 V/µs, Gate Open, T _J = 125°C, f = 500 Hz, C _L = 5.0 µF, L _L = 20 mH, No Snubber)	6.0	_	_	A/ms
dv/dt	Critical Rate of Rise of Off-State Voltage ($V_D = 0.67 \times Rated V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^{\circ}C$)	500	—	—	V/μs
di/dt	Repetitive Critical Rate of Rise of On-State Voltage	—	—	10	A/μs

1. Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

PACKAGE DIMENSIONS



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